











TS5A23166

SCDS196J-MAY 2005-REVISED SEPTEMBER 2019

TS5A23166 0.9- Ω Dual-SPST Analog Switch 5-V and 3.3-V 2-Channel Analog Switch

Features

- Isolation in Powered-Down Mode, $V_{+} = 0$
- Low ON-state resistance (0.9 Ω)
- Control inputs are 5.5-V Tolerant
- Low charge injection
- Excellent ON-state resistance matching
- Low total harmonic distortion (THD)
- 1.65-V to 5.5-V Single-supply operation
- Latch-up performance exceeds 100 mA per JESD 78, class II
- ESD Performance tested per JESD 22
 - 2000-V Human-body model (A114-B, Class II)
 - 1000-V Charged-device model (C101)

2 Applications

- Cell phones
- Portable instrumentation
- Audio and video signal routing
- Low-voltage data-acquisition systems
- Communication circuits
- Modems
- **Hard Drives**
- **Computer Peripherals**
- Wireless Terminals and Peripherals

3 Description

The TS5A23166 device is a dual single-pole singlethrow (SPST) analog switch that is designed to operate from 1.65 V to 5.5 V. The TS5A23166 device offers a low ON-state resistance and an excellent channel-to-channel ON-state resistance matching. The TS5A23166 device has excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TS5A23166	VSSOP (8)	2.30 mm × 2.00 mm
155A23100	DSBGA (8)	1.91 mm × 0.91 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic

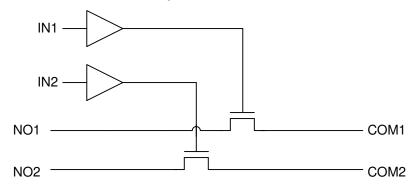




Table of Contents

2 Applications 1 8.1 Overview 8.2 Functional Block Diagram 8.2 Functional Block Diagram 8.3 Feature Description 8.4 Device Functional Modes 9.4 Device Functional Modes 9.1 Application and Implementation 9.1 Application Information 9.1 Application Information 9.2 Typical Application 9.2 Typical	18 18 19 19 20 20 20 21 21 21 21
4 Revision History	18 19 19 20 20 20 21 21 21 22
4 Revision History. 2 8.3 Feature Description. 8.4 Device Functional Modes. 9 Application and Implementation 9.1 Application Information. 9.2 Typical Application Information. 9.1 Layout Example 11.1 Layout Guidelines. 11.2 Layout Example. 11.2 Layout Example. 11.2 Layout Example. 11.2 Layout Example. 11.2 Receiving Notification of Documentation Update 6.10 Switching Characteristics: 2.5-V Supply 10 12.3 Community Resources. 12.5 Electrostatic Discharge Caution.	18 19 19 20 20 20 21 21 21
5Pin Configuration and Functions38.4Device Functional Modes6Specifications39Application and Implementation6.1Absolute Maximum Ratings39.1Application Information6.2ESD Ratings49.2Typical Application6.3Recommended Operating Conditions410Power Supply Recommendations6.4Thermal Information411Layout6.5Electrical Characteristics: 5-V Supply411.1Layout Guidelines6.6Electrical Characteristics: 2.5-V Supply611.2Layout Example6.7Electrical Characteristics: 2.5-V Supply712Device and Documentation Support6.8Electrical Characteristics: 1.8-V Supply1012.2Receiving Notification of Documentation Update6.10Switching Characteristics: 3.3-V Supply1012.3Community Resources6.11Switching Characteristics: 2.5-V Supply1012.4Trademarks6.12Switching Characteristics: 1.8-V Supply1112.5Electrostatic Discharge Caution	19 19 20 20 20 21 21 es 22
6 Specifications	19 20 20 20 20 21 21 21 22
6.1 Absolute Maximum Ratings 3 6.2 ESD Ratings 4 6.3 Recommended Operating Conditions 4 6.4 Thermal Information 4 6.5 Electrical Characteristics: 5-V Supply 4 6.6 Electrical Characteristics: 3.3-V Supply 6 6.7 Electrical Characteristics: 2.5-V Supply 7 6.8 Electrical Characteristics: 1.8-V Supply 9 6.9 Switching Characteristics: 3.3-V Supply 10 6.10 Switching Characteristics: 2.5-V Supply 10 6.11 Switching Characteristics: 2.5-V Supply 10 6.12 Switching Characteristics: 1.8-V Supply 11 6.13 Electrical Characteristics: 1.8-V Supply 10 6.14 Switching Characteristics: 1.8-V Supply 10 6.15 Electrical Characteristics: 1.8-V Supply 10 6.16 Switching Characteristics: 1.8-V Supply 10 6.17 Electrical Characteristics: 1.8-V Supply 10 6.18 Electrical Characteristics: 1.8-V Supply 10 6.19 Switching Characteristics: 1.8-V Supply 10 6.10 Switching Characteristics: 1.8-V Supply 10 6.11 Electrical Characteristics: 1.8-V Supply 10 6.12 Electrical Characteristics: 1.8-V Supply 10 6.13 Electrical Characteristics: 1.8-V Supply 10 6.14 Electrical Characteristics: 1.8-V Supply 10 6.15 Electrical Characteristics: 1.8-V Supply 10 6.16 Electrical Characteristics: 1.8-V Supply 10 6.7 Electrical Characteristics: 1.8-V Supply 10 6.9 Switching Characteristics: 1.8-V Supply 10 6.9 Electrical Characteristics: 1.8-V Supply 10 6.9 Electrical Characteristics: 1.8-V Supply 10 6.9 Switching Characteristics: 1.8-V Supply 10 6.9 Electrical Characteristics: 1.8-V Supply 10 6.9 Electri	19 20 20 20 20 21 21 es 22 22
6.2 ESD Ratings 4 6.3 Recommended Operating Conditions 4 6.4 Thermal Information 4 6.5 Electrical Characteristics: 5-V Supply 4 6.6 Electrical Characteristics: 3.3-V Supply 6 6.7 Electrical Characteristics: 2.5-V Supply 7 6.8 Electrical Characteristics: 1.8-V Supply 9 6.9 Switching Characteristics: 5-V Supply 10 6.10 Switching Characteristics: 2.5-V Supply 10 6.11 Switching Characteristics: 2.5-V Supply 10 6.12 Switching Characteristics: 1.8-V Supply 11 6.3 Power Supply Recommendations 11 Layout 11 1.1 Layout Guidelines 11 1.2 Layout Example 11 1.2 Layout Example 11 12.1 Device and Documentation Support 12.1 Device Support 12.2 Receiving Notification of Documentation Update 12.3 Community Resources 12.4 Trademarks 12.5 Electrostatic Discharge Caution 12.5 Electrostatic Discharge Caution 12.5 Electrostatic Discharge Caution 13 10 11 11 12 12 13 14 15 16 17 18 19 19 11 11 11 12 12 12 13 14 15 16 17 18 18 19 19 11 11 11 12 12 13 14 15 16 17 18 18 18 18 19 10 11 11 11 12 12 12 13 14 15 16 17 18 18 18 18 18 18 18 18 18 18 18 18 18	20 20 20 20 21 21 es 22
6.3 Recommended Operating Conditions	20 20 21 21 es 22 22
6.4 Thermal Information	20 20 21 21 es 22 22
6.5 Electrical Characteristics: 5-V Supply	20 21 21 es 22 22
6.6 Electrical Characteristics: 3.3-V Supply 6 6.7 Electrical Characteristics: 2.5-V Supply 7 6.8 Electrical Characteristics: 1.8-V Supply 9 6.9 Switching Characteristics: 5-V Supply 10 6.10 Switching Characteristics: 3.3-V Supply 10 6.11 Switching Characteristics: 2.5-V Supply 10 6.12 Switching Characteristics: 1.8-V Supply 11 6.13 Electrical Characteristics: 2.5-V Supply 10 6.14 Trademarks 12.5 Electrostatic Discharge Caution 11.2 Layout Example 11.2 Layout Example 12.1 Device and Documentation Support 12.1 Device Support 12.2 Receiving Notification of Documentation Update 12.3 Community Resources 12.4 Trademarks 12.5 Electrostatic Discharge Caution 12.5 Electrostati	21 21 es 22 22
6.7 Electrical Characteristics: 2.5-V Supply	21 s 22 22
6.8 Electrical Characteristics: 1.8-V Supply 9 12.1 Device Support Pocket Support 12.2 Receiving Notification of Documentation Update 12.3 Switching Characteristics: 3.3-V Supply 10 12.4 Trademarks 12.5 Electrostatic Discharge Caution 12.5 Electrostatic Discharge Caution 12.6 Support 12.7 Community Resources 12.7 Community Resources 12.8 V Supply 12.9 Electrostatic Discharge Caution 12.9 Electrostatic Discharge Caution 12.9 Electrostatic Discharge Caution 12.9 Community Resources 12.9 Electrostatic Discharge Caution 12.9 El	21 s 22 22
6.9 Switching Characteristics: 5-V Supply	22
6.10 Switching Characteristics: 3.3-V Supply	
6.11 Switching Characteristics: 2.5-V Supply	22
6.12 Switching Characteristics: 1.8-V Supply	
· · ·	22
6.13 Typical Characteristics	22
7 Parameter Measurement Information	. 22
Revision History OTE: Page numbers for previous revisions may differ from page numbers in the current version.	
nanges from Revision I (March 2018) to Revision J	age
Changed the Thermal Information table	4
nanges from Revision H (May 2015) to Revision I	age
Added Note: "Not tested in production" to leakage current at 25°C in the Electrical Characteristics tables	4
nanges from Revision G (February 2013) to Revision H	age
Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section	1
Updated document to new TI data sheet format - no specification changes.	1
Removed Ordering Information table.	1
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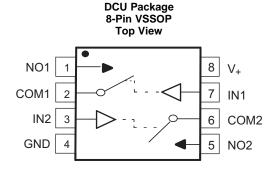
Changes from Revision F (September 2012) to Revision G

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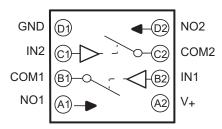
Page



5 Pin Configuration and Functions



YZT or YZP Package 8-Pin DSBGA Bottom View



Pin Functions

	PIN		TYPE	DESCRIPTION	
NAME	TSSOP NO.	DSBGA NO.	ITPE	DESCRIPTION	
COM1	2	B1	I/O	Common port for switch 1	
COM2	6	C2	I/O	Common port for switch 2	
GND	4	D1	GND	Ground	
IN1	7	B2	1	Active-high control pin connecting NO1 to COM1.	
IN2	3	C1	1	Active-high control pin connecting NO2 to COM2.	
NO1	1	A1	I/O	Normally open switch path 1	
NO2	5	D2	I/O	Normally open switch path 2	
V+	8	A2	PWR	Power supply pin	

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)(2)

			MIN	MAX	UNIT
V ₊	Supply voltage ⁽³⁾		-0.5	6.5	V
$V_{NO} \ V_{COM}$	Analog voltage (3)(4)(5)		-0.5	V ₊ + 0.5	V
I_{K}	Analog port diode current	$V_{NO}, V_{COM} < 0$	-50		mA
I _{NO}	ON-state switch current	$V_{NO, V_{COM}} = 0$ to V_{+}	-200	200	mA
I _{COM}	ON-state peak switch current ⁽⁶⁾	V_{NO} , $V_{COM} = 0$ to V_{+}	-400	400	mA
VI	Digital input voltage (3)(4)		-0.5	6.5	V
I _{IK}	Digital input clamp current	V _I < 0	-50		mA
I ₊	Continuous current through V ₊			100	mA
I _{GND}	Continuous current through GND		-100	100	mA

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 5) This value is limited to 5.5 V maximum.
- (6) Pulse at 1-ms duration < 10% duty cycle.



6.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	+2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	+1000	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _{I/O}	Input/output voltage	0	V ₊	V
V ₊	Supply voltage	1.65	5.5	V
VI	Control Input Voltage	0	5.5	V
T_A	Operating free-air temperature	-40	85	°C

6.4 Thermal Information

	Junction-to-case (top) thermal resistance Junction-to-board thermal resistance Junction-to-top characterization parameter	TS5A23166					
	THERMAL METRIC ⁽¹⁾	DCU (VSSOP)	YZP (DSBGA)	YZT (DSBGA)	UNIT		
		8 PINS	8 PINS	8 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance	212.2	99.9	99.7	°C/W		
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	77.6	1.0	1.4	°C/W		
$R_{\theta JB}$	Junction-to-board thermal resistance	91.7	27.8	27.8	°C/W		
ФЈТ	Junction-to-top characterization parameter	7.1	0.4	0.5	°C/W		
φ ЈВ	Junction-to-board characterization parameter	91.1	27.8	27.7	°C/W		

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report.

6.5 Electrical Characteristics: 5-V Supply

 $V_{+} = 4.5 \text{ V}$ to 5.5 V, $T_{A} = -40 ^{\circ}\text{C}$ to 85°C (unless otherwise noted)⁽¹⁾

	PARAMETER	TEST COND	ITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Analog Switc	h	•		•		•		•	
V _{COM} , V _{NO}	Analog signal					0		V ₊	V
_	Peak ON resistance	0 ≤ V _{NO} ≤ V ₊ ,	Switch ON,	25°C	4.5 V		0.9	1.1	Ω
r _{peak}	i can Oiv icoloidile	$I_{COM} = -100 \text{ mA},$	see Figure 11	Full	4.5 V			1.2	
	ON-state resistance	V _{NO} = 2.5 V,	Switch ON,	25°C	4.5 V		0.75	0.9	Ω
r _{on}	ON-State resistance	$I_{COM} = -100 \text{ mA},$	see Figure 11	Full	4.5 V			1	52
	ON-state resistance	$V_{NO} = 2.5 \text{ V},$	Switch ON, see Figure 11	25°C	4.5 V		0.04	0.1	
Δr_{on}	match between channels	$I_{COM} = -100 \text{ mA},$		Full				0.1	Ω
	ON-state resistance	$0 \le V_{NO} \le V_+,$ $I_{COM} = -100 \text{ mA},$	Switch ON, see Figure 11	25°C	4.5 V		0.2		Ω
r _{on(flat)}	flatness	V _{NO} = 1 V, 1.5 V, 2.5 V,	Switch ON, see Figure 11	25°C			0.15	0.25	
		$I_{COM} = -100 \text{ mA},$		Full				0.25	
		V _{NO} = 1 V,		25°C		0 V	4	20 ⁽²⁾	
I _{NO(OFF)}	NO OFF leakage current	$V_{COM} = 4.5 \text{ V},$ or $V_{NO} = 4.5 \text{ V},$ $V_{COM} = 1 \text{ V},$	Switch OFF, see Figure 12	Full	5.5 V	-150		150	nA
1		$V_{NO} = 0$ to 5.5 V, Switch OFF, $V_{COM} = 5.5$ V to 0, see Figure 12	Switch OFF,	25°C	0 V	-10	0.2	10 ⁽²⁾	
INO(PWROFF)			see Figure 12	Full		-50		50	μΑ

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

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⁽²⁾ Not tested in production.



Electrical Characteristics: 5-V Supply (continued)

 $V_{+} = 4.5 \text{ V to } 5.5 \text{ V}, T_{A} = -40^{\circ}\text{C} \text{ to } 85^{\circ}\text{C} \text{ (unless otherwise noted)}^{(1)}$

	PARAMETER	TEST COM	NDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
		V _{COM} = 1 V,		25°C		0 V	4	20 ⁽²⁾	
I _{COM(OFF)}	COM OFF leakage current	$V_{NO} = 4.5 \text{ V},$ or $V_{COM} = 4.5 \text{ V},$ $V_{NO} = 1 \text{ V},$	Switch OFF, see Figure 12	Full	5.5 V	-150		150	nA
ı		$V_{COM} = 0 \text{ to } 5.5 \text{ V},$	Switch OFF,	25°C	0 V	-10	0.2	10 ⁽²⁾	
I _{COM(PWROFF)}		$V_{NO} = 5.5 \text{ V to } 0,$	see Figure 12	Full	0 0	-50		50	μА
	,	V _{NO} = 1 V,		25°C		- 5	0.4	5 ⁽²⁾	
I _{NO(ON)}	NO ON leakage current	$V_{COM} = Open,$ or $V_{NO} = 4.5 \text{ V},$ $V_{COM} = Open,$	Switch ON, see Figure 13	Full	5.5 V	-50		50	nA
		$V_{COM} = 1 V$,		25°C		-5	0.4	5 ⁽²⁾	
I _{COM(ON)}	COM ON leakage current	$V_{NO} = Open,$ or $V_{COM} = 4.5 \text{ V},$ $V_{NO} = Open,$	Switch ON, see Figure 13	Full	5.5 V	-50		50	nA
Digital Control	Inputs (IN1, IN2) ⁽³⁾								
V _{IH}	Input logic high			Full		2.4		5.5	V
V _{IL}	Input logic low			Full		0		0.8	V
	land lanks a summer	V 55V0		25°C	5.5.1/	-2	0.3	2	^
I_{IH} , I_{IL}	Input leakage current	$V_1 = 5.5 \text{ V or } 0$		Full	5.5 V	-20		20	nA
Dynamic									
Q _C	Charge injection	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, see Figure 19	25°C	5 V		6		рС
C _{NO(OFF)}	NO OFF capacitance	$V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 14	25°C	5 V		19		pF
C _{COM(OFF)}	COM OFF capacitance	V _{COM} = V ₊ or GND, Switch OFF,	See Figure 14	25°C	5 V		18		pF
C _{NO(ON)}	NO ON capacitance	$V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 14	25°C	5 V		35.5		pF
C _{COM(ON)}	COM ON capacitance	V _{COM} = V ₊ or GND, Switch ON,	See Figure 14	25°C	5 V		35.5		pF
Cı	Digital input capacitance	$V_1 = V_+ \text{ or GND},$	See Figure 14	25°C	5 V		2		pF
BW	Bandwidth	$R_L = 50 \Omega$, Switch ON,	See Figure 16	25°C	5 V		150		MHz
O _{ISO}	OFF isolation	$R_L = 50 \ \Omega,$ $f = 1 \ MHz,$	Switch OFF, see Figure 17	25°C	5 V		-62		dB
X _{TALK}	Crosstalk	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch ON, see Figure 18	25°C	5 V		-85		dB
THD	Total harmonic distortion	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, see Figure 20	25°C	5 V).005%		
Supply									
I ₊	Positive supply	$V_1 = V_+$ or GND,	Switch ON or	25°C	5.5 V		0.01	0.1	μΑ
'+	current	VI - V+ OI GIVD,	OFF	Full				1	μА

⁽³⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



6.6 Electrical Characteristics: 3.3-V Supply

 $V_{+} = 3 \text{ V}$ to 3.6 V, $T_{A} = -40 ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$ (unless otherwise noted) $^{(1)}$

	PARAMETER	TEST CON	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switcl	h								
V _{COM} , V _{NO}	Analog signal range					0		V ₊	V
r _{peak}	Peak ON resistance	$0 \le V_{NO} \le V_+,$ $I_{COM} = -100 \text{ mA},$	Switch ON, see Figure 11	25°C Full	3 V		1.3	1.6 1.8	Ω
r _{on}	ON-state resistance	V _{NO} = 2 V, I _{COM} = -100 mA,	Switch ON, see Figure 11	25°C Full	3 V		1.1	1.5	Ω
Δr_{on}	ON-state resistance match between channels	V _{NO} = 2 V, 0.8 V, I _{COM} = -100 mA,	Switch ON, see Figure 11	25°C Full	3 V		0.04	0.1	Ω
	ON-state resistance	$0 \le V_{NO} \le V_{+},$ $I_{COM} = -100 \text{ mA}$	Switch ON, see Figure 11	25°C			0.3		Ω
r _{on(flat)}	flatness	$V_{NO} = 2 \text{ V}, 0.8 \text{ V},$ $I_{COM} = -100 \text{ mA},$	Switch ON, see Figure 11	25°C Full	3 V		0.15	0.25 0.25	
I _{NO(OFF)}	NO	$V_{NO} = 1 \text{ V}, V_{COM} = 3 \text{ V},$ or $V_{NO} = 3 \text{ V}, V_{COM} = 1 \text{ V},$	Switch OFF, see Figure 12	25°C Full	3.6 V	-5 -50	0.5	5 ⁽²⁾	nA
I _{NO(PWROFF)}	OFF leakage current	V _{NO} = 0 to 3.6 V, V _{COM} = 3.6 V to 0,	Switch OFF, see Figure 12	25°C Full	0 V	-5 -25	0.1	5 ⁽²⁾	μА
I _{COM(OFF)}	COM	$V_{COM} = 1 \text{ V}, V_{NO} = 3 \text{ V},$ or $V_{COM} = 3 \text{ V}, V_{NO} = 1 \text{ V},$	Switch OFF, see Figure 12	25°C Full	3.6 V	-5 -50	0.5	5 ⁽²⁾	nA
I _{COM(PWROFF)}	OFF leakage current	$V_{COM} = 0 \text{ to } 3.6 \text{ V},$ $V_{NO} = 3.6 \text{ V to } 0,$	Switch OFF, see Figure 12	25°C Full	0 V	-5 -25	0.1	5 ⁽²⁾ 25	μА
I _{NO(ON)}	NO	V _{NO} = 1 V, V _{COM} = Open, or	Switch ON,	25°C	3.6 V	-2	0.3	2 ⁽²⁾	nA
NO(ON)	ON leakage current	V _{NO} = 3 V, V _{COM} = Open,	see Figure 13	Full		-20	2.0	20 2 ⁽²⁾	11/5
I _{COM(ON)}	COM ON leakage current	$\begin{split} &V_{COM} = 1 \text{ V,} \\ &V_{NO} = \text{Open,} \\ &\text{or} \\ &V_{COM} = 3 \text{ V,} \\ &V_{NO} = \text{Open,} \end{split}$	Switch ON, see Figure 13	25°C Full	3.6 V	-2 -20	0.3	20	nA
Digital Contro	ol Inputs (IN1, IN2) ⁽³⁾						-		-
V _{IH}	Input logic high			Full		2		5.5	V
V_{IL}	Input logic low			Full		0		8.0	V
I _{IH} , I _{IL}	Input leakage current	V _I = 5.5 V or 0		25°C	3.6 V	-2	0.3	2	nA
H IZ TIE	iriput ieakage current	v ₁ = 5.5 v Or U		Full	3.0 V	-20		20	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

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⁽²⁾ Not tested in production.

⁽³⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



Electrical Characteristics: 3.3-V Supply (continued)

 $V_{+} = 3 \text{ V}$ to 3.6 V, $T_{A} = -40 ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$ (unless otherwise noted)⁽¹⁾

	PARAMETER	TEST CO	ONDITIONS	T _A	V ₊	MIN TYP	MAX	UNIT
Dynamic								
Q _C	Charge injection	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, see Figure 19	25°C	5 V	6		рС
C _{NO(OFF)}	NO OFF capacitance	$V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 14	25°C	3.3 V	19.5		pF
C _{COM(OFF)}	COM OFF capacitance	V _{COM} = V ₊ or GND, Switch OFF,	See Figure 14	25°C	3.3 V	18.5		pF
C _{NO(ON)}	NO ON capacitance	$V_{NO} = V_{+} \text{ or GND},$ Switch ON,	See Figure 14	25°C	3.3 V	36		pF
C _{COM(ON)}	COM ON capacitance	V _{COM} = V ₊ or GND, Switch ON,	See Figure 14	25°C	3.3 V	36		pF
Cı	Digital input capacitance	$V_I = V_+ \text{ or GND},$	See Figure 14	25°C	3.3 V	2		pF
BW	Bandwidth	$R_L = 50 \Omega$, Switch ON,	See Figure 16	25°C	3.3 V	150		MHz
O _{ISO}	OFF isolation	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch OFF, see Figure 17	25°C	3.3 V	-62		dB
X _{TALK}	Crosstalk	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch ON, see Figure 18	25°C	3.3 V	-85		dB
THD	Total harmonic distortion	$R_L = 600 \Omega,$ $C_L = 50 \text{ pF},$	f = 20 Hz to 20 kHz, see Figure 20	25°C	3.3 V	0.01%		
Supply								
1	Positive supply	V = V or GND	Switch ON or OFF	25°C	3.6 V	0.001	0.05	^
I ₊	current	$V_1 = V_+$ or GND, Switch ON or OFF	Full	3.6 V		0.3	μΑ	

6.7 Electrical Characteristics: 2.5-V Supply

 $V_{+} = 2.3 \text{ V to } 2.7 \text{ V}, T_{A} = -40 ^{\circ}\text{C} \text{ to } 85 ^{\circ}\text{C} \text{ (unless otherwise noted)}^{(1)}$

PAI	RAMETER	TEST CO	ONDITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Analog Switch	n								
V _{COM} , V _{NO}	Analog signal range					0		V ₊	V
_	Peak ON	$0 \le V_{NO} \le V_+,$	Switch ON,	25°C	2.3 V		1.8	2.4	Ω
r _{peak}	resistance	$I_{COM} = -8 \text{ mA},$	see Figure 11	Full	2.3 V			2.6	12
	ON-state	$V_{NO} = 1.8 \text{ V},$	Switch ON,	25°C	2.3 V		1.2	2.1	Ω
r _{on}	resistance	$I_{COM} = -8 \text{ mA},$	see Figure 11	Full	2.3 V			2.4	77
	ON-state			25°C			0.04	0.15	
Δr_{on}	resistance match between channels	$V_{NO} = 1.8 \text{ V}, 0.8 \text{ V},$ $I_{COM} = -8 \text{ mA},$	Switch ON, see Figure 11	Full	2.3 V			0.15	Ω
	ON-state	$0 \le V_{NO} \le V_{+},$ $I_{COM} = -8 \text{ mA},$	Switch ON, see Figure 11	25°C	2.3 V		0.7		
r _{on(flat)}	resistance flatness	$V_{NO} = 1.8 \text{ V}, 0.8 \text{ V},$	Switch ON,	25°C			0.4	0.6	Ω
	au.rece	$I_{COM} = -8 \text{ mA},$	see Figure 11	Full				0.6	
		$V_{NO} = 0.5 V,$		25°C		- 5	0.3	5 ⁽²⁾	
I _{NO(OFF)}	NO OFF leakage	$\begin{aligned} &V_{COM} = 2.3 \text{ V,} \\ &\text{or} \\ &V_{NO} = 2.3 \text{ V,} \\ &V_{COM} = 0.5 \text{ V,} \end{aligned}$	Switch OFF, see Figure 12	Full	2.7 V	-50		50	nA
	Sanon	$V_{NO} = 0 \text{ to } 2.7 \text{ V},$	Switch OFF,	25°C	0 V -2 -15	0.05	2(2)		
I _{NO(PWROFF)}		$V_{COM} = 2.7 \text{ V to 0},$ see Figure 12	see Figure 12	Full		-15		15	μА

⁽¹⁾ The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

⁽²⁾ Not tested in production.



Electrical Characteristics: 2.5-V Supply (continued)

 $V_{+} = 2.3 \text{ V}$ to 2.7 V, $T_{A} = -40 ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$ (unless otherwise noted)⁽¹⁾

PAF	RAMETER	TEST CO	ONDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
		V _{NO} = 2.3 V,		25°C		-5	0.3	5 ⁽²⁾	
I _{COM(OFF)}	COM OFF leakage current	$\begin{split} &V_{COM} = 0.5 \text{ V},\\ &\text{or}\\ &V_{NO} = 0.5 \text{ V},\\ &V_{COM} = 2.3 \text{ V}, \end{split}$	Switch OFF, see Figure 12	Full	2.7 V	-50		50	nA
I _{COM(PWROFF)}	ou.rom	$V_{COM} = 0 \text{ to } 2.7 \text{ V},$	Switch OFF,	25°C	0 V	-2	0.05	2 ⁽²⁾	μА
*COM(PWROFF)		$V_{NO} = 2.7 \text{ V to } 0,$	see Figure 12	Full		-15		15	μ.
I _{NO(ON)}	NO ON leakage current	$\begin{aligned} &V_{NO} = 0.5 \text{ V}, \\ &V_{COM} = \text{Open}, \\ &\text{or} \\ &V_{NO} = 2.3 \text{ V}, \\ &V_{COM} = \text{Open}, \end{aligned}$	Switch ON, see Figure 13	25°C Full	2.7 V	-2 -20	0.3	20	nA
I _{COM(ON)}	COM ON leakage current	$\begin{aligned} &V_{\text{COM}} = 0.5 \text{ V,} \\ &V_{\text{NO}} = \text{Open,} \\ &\text{or} \\ &V_{\text{COM}} = 2.3 \text{ V,} \\ &V_{\text{NO}} = \text{Open,} \end{aligned}$	Switch ON, see Figure 13	25°C Full	2.7 V	-2 -20	0.3	2 ⁽²⁾	nA
Digital Control	Inputs (IN1, IN2)	v _{NO} – Open,							
V _{IH}	Input logic high			Full		1.8		5.5	V
V _{IL}	Input logic low			Full		0		0.6	V
	Input leakage	V 55V0		25°C	0.7.1/	-2	0.3	2	A
I _{IH} , I _{IL}	current	V _I = 5.5 V or 0		Full	2.7 V	-20		20	nA
Dynamic									
Q_C	Charge injection	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, see Figure 19	25°C	2.5 V		4		pC
$C_{\text{NO(OFF)}}$	NO OFF capacitance	V _{NO} = V ₊ or GND, Switch OFF,	See Figure 14	25°C	2.5 V		19.5		pF
$C_{\text{COM(OFF)}}$	COM OFF capacitance	V _{COM} = V ₊ or GND, Switch OFF,	See Figure 14	25°C	2.5 V		18.5		pF
C _{NO(ON)}	NO ON capacitance	V _{NO} = V ₊ or GND, Switch ON,	See Figure 14	25°C	2.5 V		36.5		pF
C _{COM(ON)}	COM ON capacitance	V _{COM} = V ₊ or GND, Switch ON,	See Figure 14	25°C	2.5 V		36.5		pF
Cı	Digital input capacitance	$V_I = V_+ \text{ or GND},$	See Figure 14	25°C	2.5 V		2		pF
BW	Bandwidth	$R_L = 50 \Omega$, Switch ON,	See Figure 16	25°C	2.5 V		150		MHz
O _{ISO}	OFF isolation	$R_L = 50 \Omega$, f = 1 MHz,	Switch OFF, see Figure 17	25°C	2.5 V		-62		dB
X _{TALK}	Crosstalk	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, see Figure 18	25°C	2.5 V		-85		dB
THD	Total harmonic distortion	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, see Figure 20	25°C	2.5 V		0.02%		
Supply			<u>'</u>		<u> </u>			<u> </u>	
I ₊	Positive supply	$V_1 = V_+ \text{ or GND},$	Switch ON or OFF	25°C	2.7 V		0.001	0.02	μА
-+	current	1, 1, 0, 0, 10,	J 311 01 01 1	Full	•			0.25	h., ,

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6.8 Electrical Characteristics: 1.8-V Supply

 $V_{+} = 1.65 \text{ V}$ to 1.95 V, $T_{A} = -40 ^{\circ}\text{C}$ to 85°C (unless otherwise noted)⁽¹⁾

PAR	RAMETER	TEST CO	ONDITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Analog Switch	 1				•				
V _{COM} , V _{NO}	Analog signal range					0		V ₊	٧
r peak	Peak ON resistance	$0 \le V_{NO} \le V_{+},$ $I_{COM} = -2 \text{ mA},$	Switch ON, see Figure 11	25°C Full	1.65 V		4.2	25 30	Ω
- on	ON-state resistance	$V_{NO} = 0.6 \text{ V}, 1.5 \text{ V},$ $I_{COM} = -2 \text{ mA},$	Switch ON, see Figure 11	25°C	1.65 V		1.6	3.9	Ω
		ICOM = Z IIIV,	3cc rigure rr	Full			0.04	4	
∆r _{on}	ON-state resistance match between channels	$V_{NO} = 1.5 \text{ V},$ $I_{COM} = -2 \text{ mA},$	Switch ON, see Figure 11	25°C Full	1.65 V		0.04	0.2	Ω
	ON-state	$0 \le V_{NO} \le V_{+},$ $I_{COM} = -2 \text{ mA},$	Switch ON, see Figure 11	25°C	1.65 V		2.8		_
on(flat)	resistance flatness	V _{NO} = 0.6 V, 1.5 V,	Switch ON,	25°C			4.1	22	Ω
		$I_{COM} = -2 \text{ mA},$	see Figure 11	Full				27	
		V _{NO} = 0.3 V,		25°C		-5	0.3	5 ⁽²⁾	
I _{NO(OFF)}	NO OFF leakage current	$V_{COM} = 1.65 \text{ V},$ or $V_{NO} = 1.65 \text{ V},$ $V_{COM} = 0.3 \text{ V},$	Switch OFF, see Figure 12	Full	1.95 V	-50		50	nA
	Current	$V_{NO} = 0 \text{ to } 1.95 \text{ V},$	Switch OFF,	25°C		-2	0.05	2 ⁽²⁾	_
NO(PWROFF)		$V_{COM} = 1.95 \text{ V to 0},$	see Figure 12	Full	0 V	-10		10	μА
		V _{NO} = 1.65 V,		25°C		-5	0.3	5 ⁽²⁾	
COM(OFF)	COM OFF leakage	$V_{COM} = 0.3 \text{ V},$ or $V_{NO} = 0.3 \text{ V},$ $V_{COM} = 1.65 \text{ V},$	Switch OFF, see Figure 12	Full	1.95 V	-50		50	nA
	current	V _{COM} = 0 to 1.95 V,	Switch OFF,	25°C		-2	0.05	⁽²⁾ 2	
COM(PWROFF)		$V_{NO} = 1.95 \text{ V to } 0,$	see Figure 12	Full	0 V	-10		10	μΑ
		V _{NO} = 0.3 V,		25°C		-2	0.3	2 ⁽²⁾	
NO(ON)	NO ON leakage current	$V_{COM} = Open,$ or $V_{NO} = 1.65 V,$ $V_{COM} = Open,$	Switch ON, see Figure 13	Full	1.95 V	-20		20	nA
		V _{NO} = Open,		25°C		-2	0.3	2	
СОМ(ОМ)	COM ON leakage current	$V_{COM} = 0.3 \text{ V},$ or $V_{NO} = \text{Open},$ $V_{COM} = 1.65 \text{ V},$	Switch ON, see Figure 13	Full	1.95 V	-20		20	nA
Digital Contro	l Inputs (IN1, IN2)	•			•				
/ _{IH}	Input logic high			Full		1.5		5.5	V
V _{IL}	Input logic low			Full		0		0.6	V
	Input leakage	V 55V 3		25°C	4.05.17	-2	0.3	2	
I _{IH} , I _{IL}	current	$V_{I} = 5.5 \text{ V or } 0$		Full	1.95 V	-20		20	μА
Dynamic		•		, l				Į.	
Q _C	Charge injection	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, see Figure 19	25°C	1.8 V		2		pC
C _{NO(OFF)}	NO OFF capacitance	V _{NO} = V ₊ or GND, Switch OFF,	See Figure 14	25°C	1.8 V		19.5		pF
C _{COM(OFF)}	COM OFF capacitance	V _{COM} = V ₊ or GND, Switch OFF,	See Figure 14	25°C	1.8 V		18.5		pF
C _{NO(ON)}	NO ON capacitance	$V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 14	25°C	1.8 V		36.5		pF

⁽¹⁾ The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

⁽²⁾ Not tested in production.



Electrical Characteristics: 1.8-V Supply (continued)

 $V_{+} = 1.65 \text{ V}$ to 1.95 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)⁽¹⁾

PA	RAMETER	TEST CO	ONDITIONS	T _A	V ₊	MIN TYP	MAX	UNIT
C _{COM(ON)}	COM ON capacitance	V _{COM} = V ₊ or GND, Switch ON,	See Figure 14	25°C	1.8 V	36.5		pF
Cı	Digital input capacitance	$V_I = V_+ \text{ or GND},$	See Figure 14	25°C	1.8 V	2		pF
BW	Bandwidth	$R_L = 50 \Omega$, Switch ON,	See Figure 16	25°C	1.8 V	150		MHz
O _{ISO}	OFF isolation	$R_L = 50 \Omega$, f = 1 MHz,	Switch OFF, see Figure 17	25°C	1.8 V	-62		dB
THD	Total harmonic distortion	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, see Figure 20	25°C	1.8 V	0.055%		
Supply								
	Positive supply	V V or CND	Switch ON or OFF	25°C	4.0F.V	0.001	0.01	
1+	current	$V_1 = V_+ \text{ or GND},$	Switch ON or OFF	Full	1.95 V		0.15	μА

6.9 Switching Characteristics: 5-V Supply

 $V_{+} = 4.5 \text{ V to } 5.5 \text{ V}, T_{A} = -40^{\circ}\text{C} \text{ to } 85^{\circ}\text{C} \text{ (unless otherwise noted)}^{(1)}$

	PARAMETER	TES	ST CONDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynai	mic								
	Turnon time	$V_{COM} = V_+,$	C _L = 35 pF,	25°C	5 V	1	4.5	7.5	no
t _{ON}	rumon ume	$R_L = 50 \Omega$,	$c_L = 50 \Omega$, see Figure 15		4.5 V to 5.5 V	1		9	ns
	Turnoff time	$V_{COM} = V_+,$	$C_L = 35 pF$,	25°C	5 V	4.5	8	11	no
t _{OFF}	rumon ume	$R_L = 50 \Omega$,	see Figure 15	Full	4.5 V to 5.5 V	3.5		13	ns

⁽¹⁾ The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

6.10 Switching Characteristics: 3.3-V Supply

 $V_{+} = 3 \text{ V}$ to 3.6 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)⁽¹⁾

	PARAMETER	TEST	CONDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynam	nic								
		V - V	$C_1 = 35 \text{ pF},$	25°C	3.3 V	1.5	5	9.5	
t _{ON}	Turnon time		see Figure 15	Full	3 V to 3.6 V	1		10	ns
			0 25 25	25°C	3.3 V	4.5	8.5	11	
t _{OFF}	Turnoff time	$ \begin{array}{lll} V_{\text{COM}} = V_{+}, & C_{L} = 35 \text{ pF}, \\ R_{L} = 50 \ \Omega, & \text{see Figure 15} \end{array} $		Full	3 V to 3.6 V	3		12.5	ns

⁽¹⁾ The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

6.11 Switching Characteristics: 2.5-V Supply

 $V_{+} = 2.3 \text{ V to } 2.7 \text{ V}, T_{A} = -40^{\circ}\text{C} \text{ to } 85^{\circ}\text{C} \text{ (unless otherwise noted)}^{(1)}$

	PARAMETER	TEST	CONDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynam	ic								
		V - V	C - 25 nE	25°C	2.5 V	2	6	10	
t _{ON}	Turnon time	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	$C_L = 35 \text{ pF},$ see Figure 15	Full	2.3 V to 2.7 V	1		12	ns
			0 25 5	25°C	2.5 V	4.5	8	12.5	
t _{OFF}	Turnoff time	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	$C_L = 35 \text{ pF},$ see Figure 15	Full	2.3 V to 2.7 V	3		15	ns

(1) The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.



6.12 Switching Characteristics: 1.8-V Supply

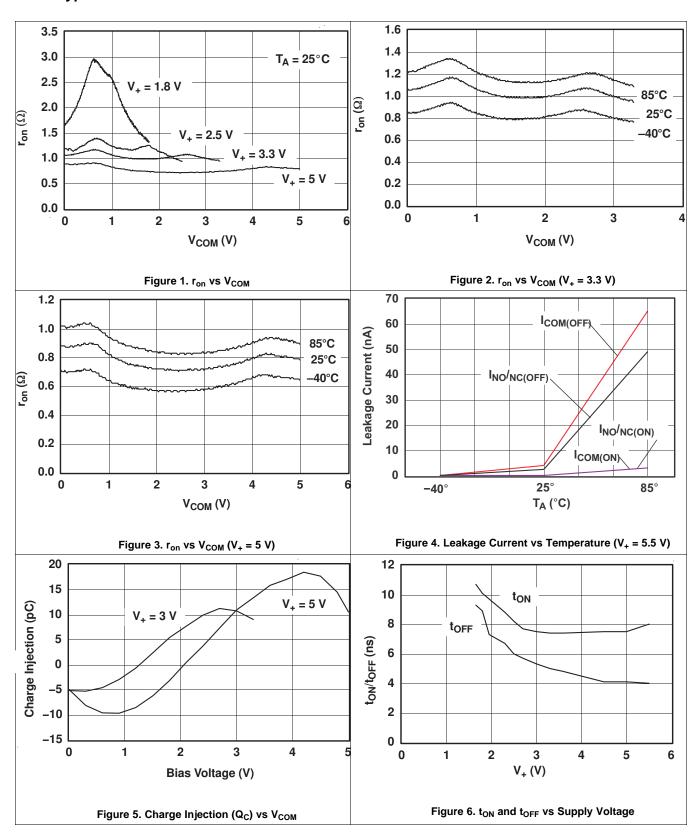
 $V_{+} = 1.65 \text{ V}$ to 1.95 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)⁽¹⁾

	PARAMETER	TES	CONDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynan	nic								
		V V	0 25 75	25°C	1.8 V	3	9	18	
t _{ON}	Turnon time	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, see Figure 15	Full	1.65 V to 1.95 V	1		20	ns
		V V	0 25 75	25°C	1.8 V	5	10	15.5	
t _{OFF}	Turnoff time	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, see Figure 15	Full	1.65 V to 1.95 V	4		18.5	ns

⁽¹⁾ The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

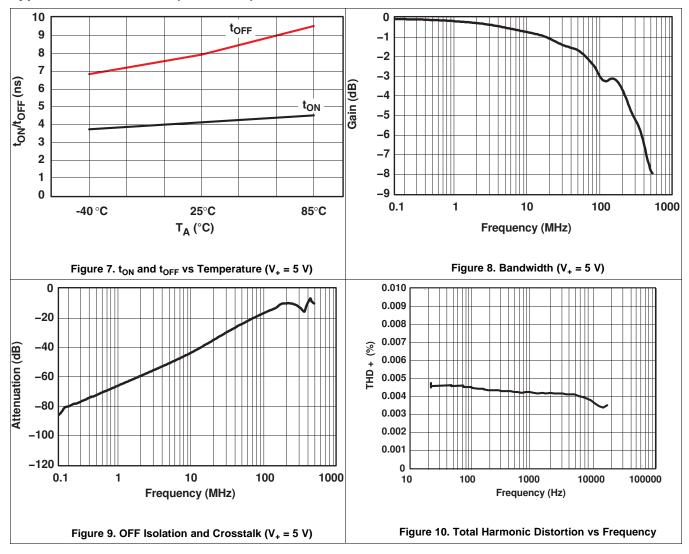


6.13 Typical Characteristics





Typical Characteristics (continued)





7 Parameter Measurement Information

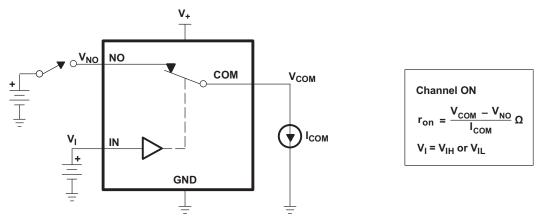


Figure 11. ON-State Resistance (ron)

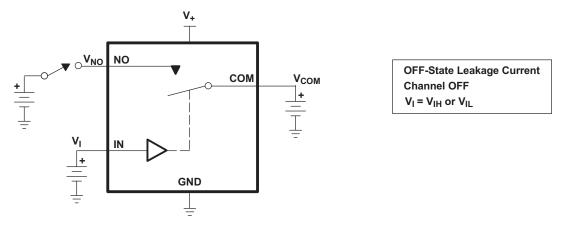


Figure 12. OFF-State Leakage Current ($I_{COM(OFF)}$, $I_{NC(OFF)}$, $I_{COM(PWROFF)}$, $I_{NC(PWR(FF))}$)

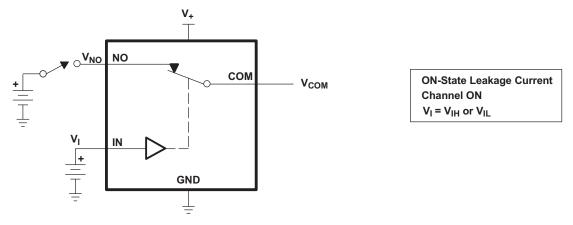


Figure 13. ON-State Leakage Current (I_{COM(ON)}, I_{NC(ON)})



Parameter Measurement Information (continued)

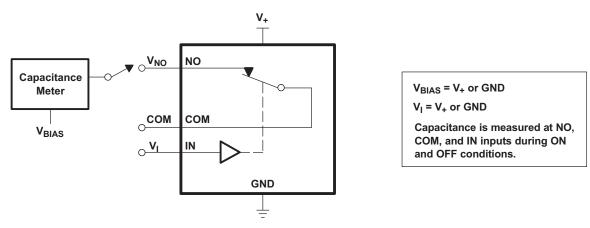
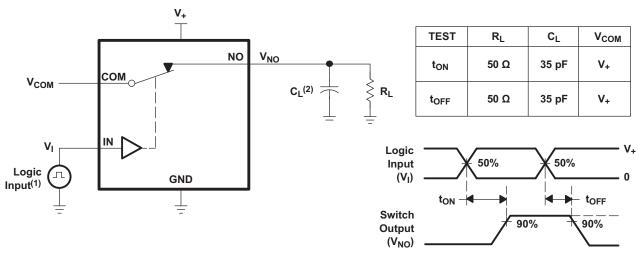


Figure 14. Capacitance (C_I, $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NC(ON)}$)



- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 $\Omega,\,t_f$ < 5 ns, t_f < 5 ns.
- (2) C_L includes probe and jig capacitance.

Figure 15. Turnon (t_{ON}) and Turnoff Time (t_{OFF})

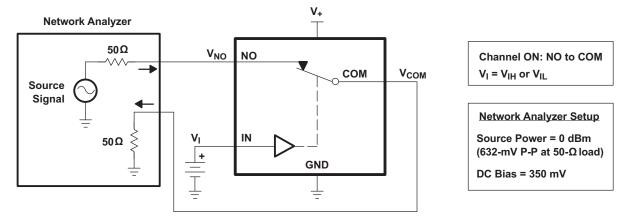
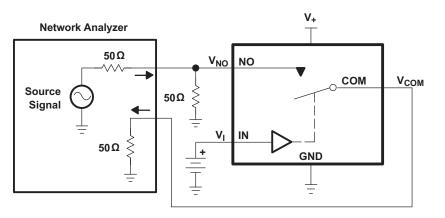


Figure 16. Bandwidth (BW)



Parameter Measurement Information (continued)



Channel OFF: NO to COM
V_I = V₊ or GND

Network Analyzer Setup

Source Power = 0 dBm (632-mV P-P at 50-Ωload) DC Bias = 350 mV

Figure 17. OFF Isolation (O_{ISO})

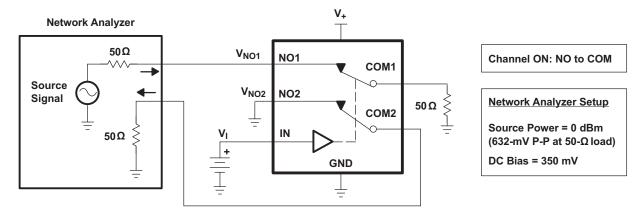
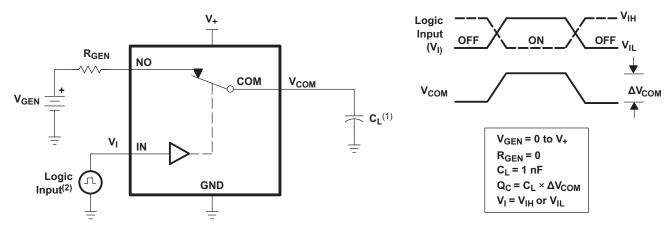


Figure 18. Crosstalk (X_{TALK})

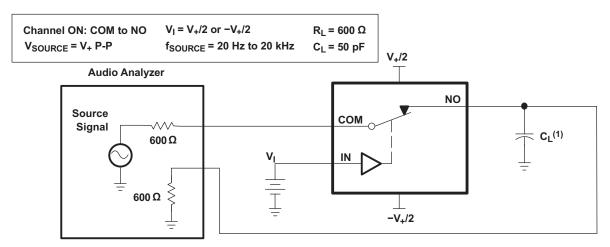


- (1) C_L includes probe and jig capacitance.
- (2) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r < 5 ns, t_f < 5 ns.

Figure 19. Charge Injection (Q_C)



Parameter Measurement Information (continued)



(1) C_L includes probe and jig capacitance.

Figure 20. Total Harmonic Distortion (THD)

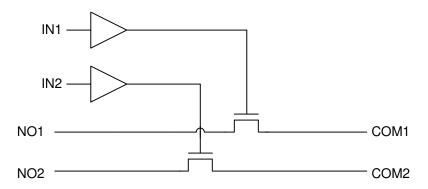


8 Detailed Description

8.1 Overview

The TS5A23166 is a dual single-pole single-throw (SPST) analog switch that is designed to operate from 1.65 V to 5.5 V. The device offers a low ON-state resistance. The device has excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications. Table 2 shows the descriptions of each parameter specified in the datasheet.

8.2 Functional Block Diagram



8.3 Feature Description

Tolerant control inputs allow 5-V logic levels to be present on the IN pin at any value of V_{CC}. Low ON-resistance allows minimal signal distortion through device.

8.4 Device Functional Modes

Table 1 shows the functional modes for TS5A23166.

Table 1. Function Table

IN	NO TO COM, COM TO NO
L	OFF
Н	ON



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TS5A23166 dual SPST analog switch is a basic component that could be used in any electrical system design. One example application is a gain selector, which is described in the *Typical Application* section.

9.2 Typical Application

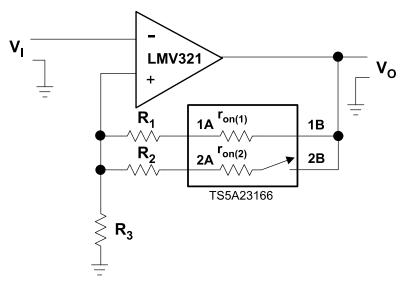


Figure 21. Gain-Control Circuit for OP Amplifier

9.2.1 Design Requirements

By selecting values of R1 and R2, such that $Rx >> r_{on(x)}$, r_{on} of TS5A23166 can be ignored. The gain of op amp can be calculated as follow:

$$Vo / VI = 1 + R|| / R3$$
 (1)

$$R|| = (R1 + r_{on(1)}) || (R2 + r_{on(2)})$$
(2)

9.2.2 Detailed Design Procedure

Place a switch in series with the input of the op amp. Because the op amp input impedance is very large, a switch on $r_{on(1)}$ is irrelevant.

TEXAS INSTRUMENTS

Typical Application (continued)

9.2.3 Application Curve

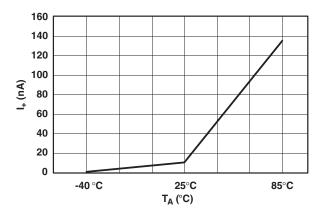


Figure 22. Power-Supply Current vs Temperature ($V_{+} = 5 \text{ V}$)

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μF bypass capacitor is recommended. If there are multiple pins labeled V_{CC} , then a 0.01- μF or 0.022- μF capacitor is recommended for each V_{CC} because the VCC pins will be tied together internally. For devices with dual supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μF bypass capacitor is recommended for each supply pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- μF and 1- μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to loop antenna theory, but different enough to warrant their own discussion. When a PCB trace turns a corner at a 90° angle, a reflection can occur. This is primarily due to the change of width of the trace. At the apex of the turn, the trace width is increased to 1.414 times its width. This upsets the transmission line characteristics, especially the distributed capacitance and self–inductance of the trace — resulting in the reflection. It is a given that not all PCB traces can be straight, and so they will have to turn corners. Figure 23 shows progressively better techniques of rounding corners. Only the last example maintains constant trace width and minimizes reflections.

11.2 Layout Example

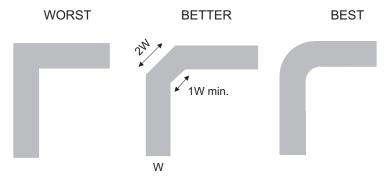


Figure 23. Trace Example



12 Device and Documentation Support

12.1 Device Support

12.1.1 Device Nomenclature

Table 2. Parameter Description

SYMBOL	DESCRIPTION
V _{COM}	Voltage at COM
V _{NO}	Voltage at NO
r _{on}	Resistance between COM and NO ports when the channel is ON
r _{peak}	Peak on-state resistance over a specified voltage range
r _{on(flat)}	Difference between the maximum and minimum value of ron in a channel over the specified range of conditions
I _{NO(OFF)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF-state under worst-case input and output conditions
I _{NO(PWROFF)}	Leakage current measured at the NO port during the power-down condition, $V_{+} = 0$
I _{COM(OFF)}	Leakage current measured at the COM port, with the corresponding channel (COM to NO) in the OFF-state under worst-case input and output conditions
I _{COM(PWROFF)}	Leakage current measured at the COM port during the power-down condition, $V_{+} = 0$
I _{NO(ON)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON-state and the output (COM) open
I _{COM(ON)}	Leakage current measured at the COM port, with the corresponding channel (COM to NO) in the ON-state and the output (NO) open
V _{IH}	Minimum input voltage for logic high for the control input (IN)
V _{IL}	Maximum input voltage for logic low for the control input (IN)
VI	Voltage at the control input (IN)
I _{IH} , I _{IL}	Leakage current measured at the control input (IN)
t _{ON}	Turnon time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM or NO) signal when the switch is turning ON.
t _{OFF}	Turnoff time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM or NO) signal when the switch is turning OFF.
$Q_{\mathbb{C}}$	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NO or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_{COM}$, C_L is the load capacitance, and ΔV_{COM} is the change in analog output voltage.
C _{NO(OFF)}	Capacitance at the NO port when the corresponding channel (NO to COM) is OFF
C _{COM(OFF)}	Capacitance at the COM port when the corresponding channel (COM to NO) is OFF
C _{NO(ON)}	Capacitance at the NO port when the corresponding channel (NO to COM) is ON
C _{COM(ON)}	Capacitance at the COM port when the corresponding channel (COM to NO) is ON
C _I	Capacitance of control input (IN)
O _{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NO to COM) in the OFF state.
BW	Bandwidth of the switch. This is the frequency in which the gain of an ON channel is -3 dB below the DC gain.
THD	Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.
I ₊	Static power-supply current with the control (IN) pin at V ₊ or GND



12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Community Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





6-Feb-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A23166DCUR	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	(AM, JAMQ, JAMR) JZ	Samples
TS5A23166DCURG4	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	JAMR	Samples
TS5A23166YZPR	ACTIVE	DSBGA	YZP	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(JM7, JMN)	Samples
TS5A23166YZTR	ACTIVE	DSBGA	YZT	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(JM7, JMN)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and



PACKAGE OPTION ADDENDUM

6-Feb-2020

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 17-Apr-2020

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A23166DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.05	3.3	1.0	4.0	8.0	Q3
TS5A23166DCUR	VSSOP	DCU	8	3000	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
TS5A23166DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
TS5A23166YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1
TS5A23166YZTR	DSBGA	YZT	8	3000	178.0	9.2	1.02	2.02	0.75	4.0	8.0	Q1

www.ti.com 17-Apr-2020



*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A23166DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
TS5A23166DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
TS5A23166DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
TS5A23166YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0
TS5A23166YZTR	DSBGA	YZT	8	3000	220.0	220.0	35.0



DIE SIZE BALL GRID ARRAY



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



NOTES:

- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-187 variation CA.



DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



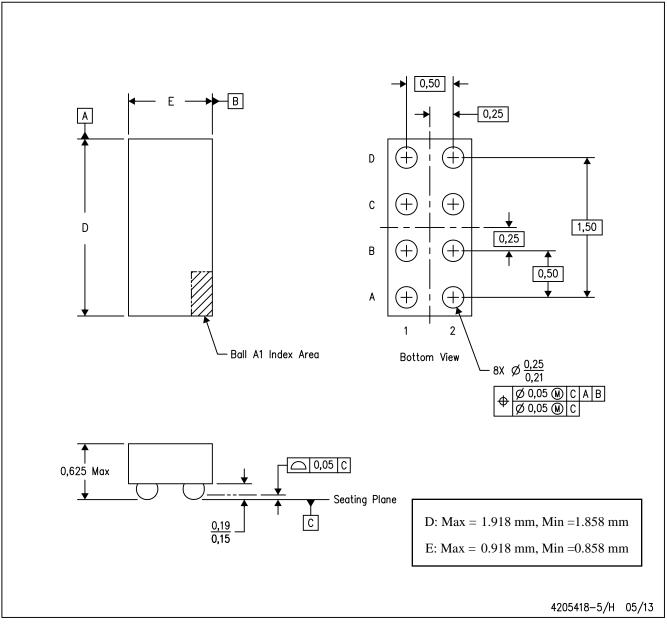
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



YZT (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.



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